Nch 30V 39A Middle Power MOSFET

V_{DSS}	30V
R _{DS(on)} (Max.)	4.3mΩ
I _D	±39A
P_D	20W

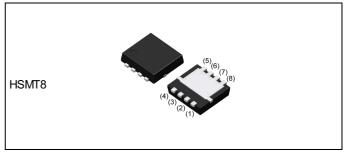
Features

- 1) Low on resistance.
- 2) High Power Package (HSMT8).
- 3) Pb-free lead plating; RoHS compliant.
- 4) Halogen Free.

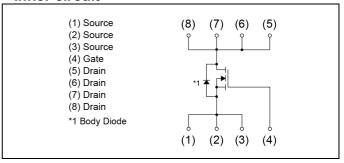
Application

Switching

Outline



●Inner circuit



Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	330
Туре	Tape width (mm)	12
	Basic ordering unit (pcs)	3000
	Taping code	TB
	Marking	E180GN

● **Absolute maximum ratings** (T_a = 25°C ,unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source voltage	V _{DSS}	30	V	
Continuous dusin summent	T _c = 25°C	I _D *1	±39	Α
Continuous drain current	T _a = 25°C	I _D	±18	Α
Pulsed drain current	I _{DP} *2	±72	Α	
Gate - Source voltage	V_{GSS}	±20	V	
Avalanche current, single pulse		I _{AS} *3	21	Α
Avalanche energy, single pulse	E _{AS} *3	32.4	mJ	
		P _D *1	20	W
Power dissipation		P _D *4	2.0	W
Junction temperature	T _j	150	°C	
Operating junction and storage te	mperature range	T _{stg}	-55 to +150	°C

●Thermal resistance

Doromotor	Curah al	Values			I India
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal resistance, junction - case	R _{thJC} *1	-	-	6.2	°C/W
Thermal resistance, junction - ambient	R _{thJA} *4	-	-	62.5	°C/W

● Electrical characteristics (T_a = 25°C)

Doromotor	Symbol	Symbol Conditions		Values			
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit	
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$, $I_D = 1mA$	30	-	-	V	
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}} I_{D} = 1 \text{mA}$ referenced to 25°C		-	28	-	mV/°C	
Zero gate voltage drain current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V	1	1	1	μA	
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	ı	1	±100	nA	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1mA$	1.2	-	2.5	V	
Gate threshold voltage temperature coefficient	$\frac{\DeltaV_{GS(th)}}{\DeltaT_j}$	I _D = 1mA referenced to 25°C	-	-3.87	-	mV/°C	
Static drain - source	D *5	V _{GS} = 10V, I _D = 18A	-	3.3	4.3	C	
on - state resistance	R _{DS(on)} *5	V _{GS} = 4.5V, I _D = 18A	-	4.3	6.1	mΩ	
Gate resistance	R_G	f=1MHz, open drain	ı	1.3	-	Ω	
Forward Transfer Admittance	Y _{fs} *5	V _{DS} = 5V, I _D = 18A	17	-	-	S	

^{*1} Tc=25°C, Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} L \simeq 0.1mH, V_{DD} = 15V, R_G = 25 Ω , STARTING T $_{j}$ = 25 $^{\circ}$ C Fig.3-1,3-2

^{*4} Mounted on a Cu board (40×40×0.8mm)

^{*5} Pulsed

● Electrical characteristics (T_a = 25°C)

Daramatar	Conditions Conditions		Values			Unit	
Parameter	Symbol	nbol Conditions		Тур.	Max.	Unit	
Input capacitance	C _{iss}	V _{GS} = 0V	-	1520	-		
Output capacitance	C _{oss}	V _{DS} = 15V	-	380	-	pF	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	117	-		
Turn - on delay time	t _{d(on)} *5	V _{DD} ≈ 15V,V _{GS} = 10V	-	16.5	-		
Rise time	t _r *5	I _D = 9A	-	6.9	-		
Turn - off delay time	t _{d(off)} *5	R _L ≃ 1.67Ω	-	56.8	-	ns	
Fall time	t _f *5	$R_G = 10\Omega$	-	10.2	-		

● Gate charge characteristics (T_a = 25°C)

	\ a	,					
Parameter	Curredo e l	Conditi	Conditions		Values		
Parameter	Symbol	I Conditions		Min.	Тур.	Max.	Unit
Total gate charge	O *5		V _{GS} = 10V	-	22.4	-	
Total gate charge	Q_g^{*5}	V _{DD} ≃ 15V		-	11.0	-	C
Gate - Source charge	Q _{gs} *5	I _D = 18A	V _{GS} = 4.5V	-	4.6	-	nC
Gate - Drain charge	Q _{gd} *5			-	3.1	-	

● Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Darameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol	ool Conditions		Тур.	Max.	Offic
Continuous forward current	I _S	T = 25°C	1	-	1.67	Α
Pulse forward current	I _{SP} *2	T _a = 25°C	-	-	72	Α
Forward voltage	V _{SD} *5	V _{GS} = 0V, I _S = 1.67A	-	-	1.2	V
Reverse recovery time	t _{rr} *5	I _S = 18A, V _{GS} =0V	-	27.6	-	ns
Reverse recovery charge	Q _{rr} *5	di/dt = 100A/μs	-	19.9	-	nC

Fig.1 Power Dissipation Derating Curve

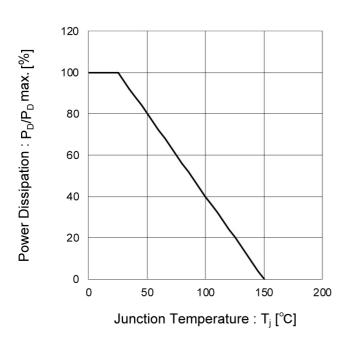
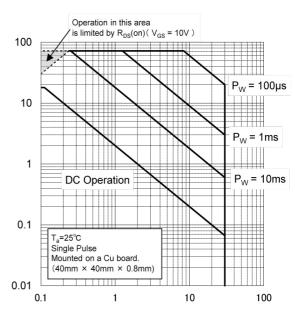


Fig.2 Maximum Safe Operating Area



Drain Current : I_D [A]

Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

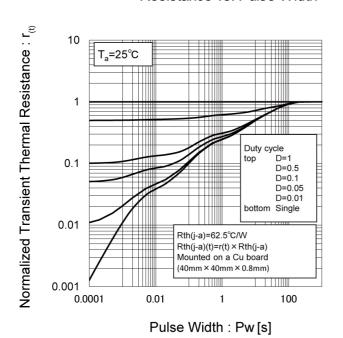
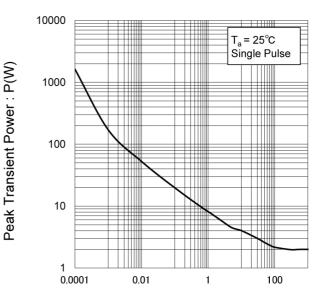


Fig.4 Single Pulse Maximum Power dissipation

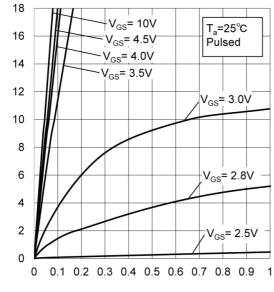


Pulse Width: Pw[s]

Drain Current : I_D [A]

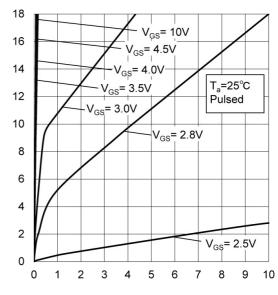
Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)



Drain - Source Voltage : V_{DS} [V]

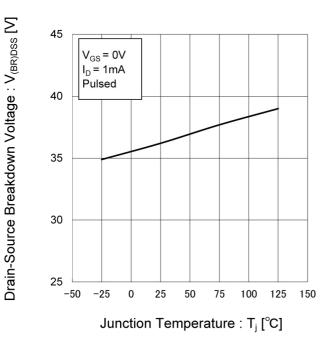
Fig.6 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

Fig.8 Typical Transfer Characteristics

Fig.7 Breakdown Voltage vs. Junction Temperature



Drain Current : I_D [A]

Drain Current : I_D [A]

100 V_{DS}= V_{GS} Pulsed 10 T_a= 125°C ≥ T_a= 75°C = T_a= 25°C T_a= - 25°C 0.1 0.01 0.001 0 0.5 1.5 2.5 3

3.5

Gate - Source Voltage : V_{GS} [V]

Fig.9 Gate Threshold Voltage vs. Junction Temperature

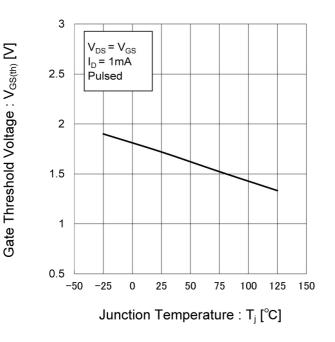


Fig.10 Forward Transfer Admittance vs. Drain Current

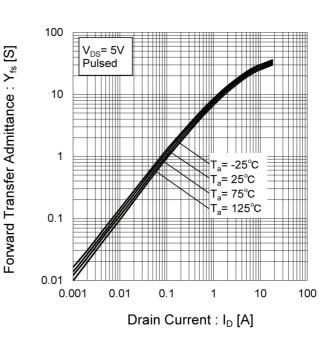


Fig.11 Drain Current Derating Curve

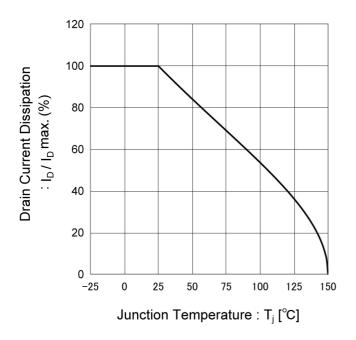


Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

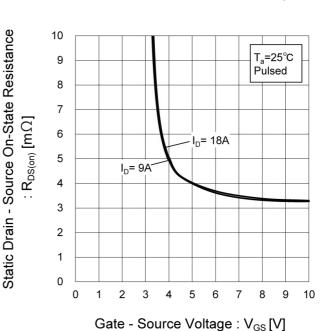


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

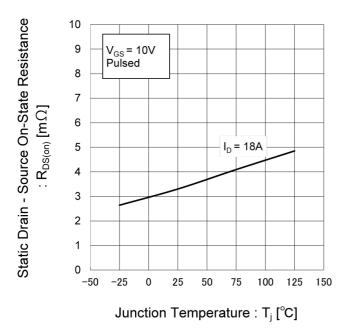


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current(I)

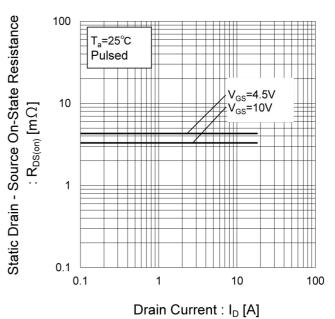


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)

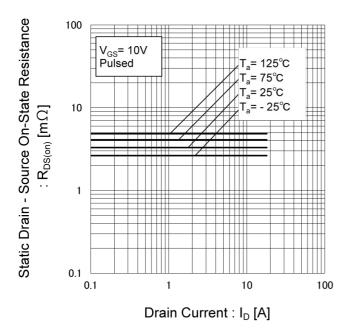


Fig.16 Static Drain - Source On - State Resistance vs. Drain Current(III)

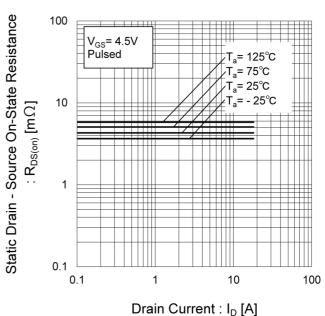


Fig.17 Typical Capacitance vs. Drain - Source Voltage

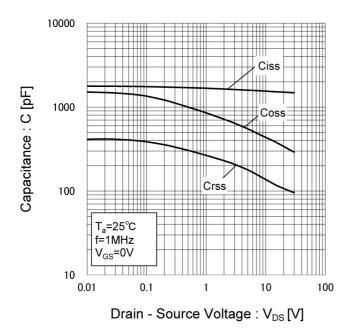


Fig.18 Switching Characteristics

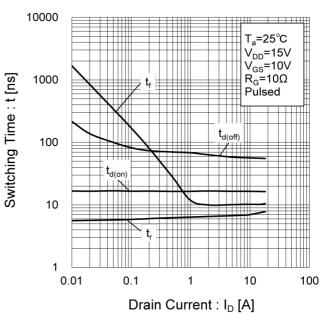


Fig.19 Dynamic Input Characteristics

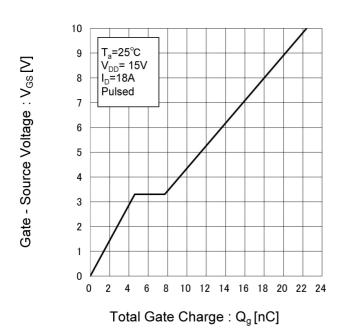
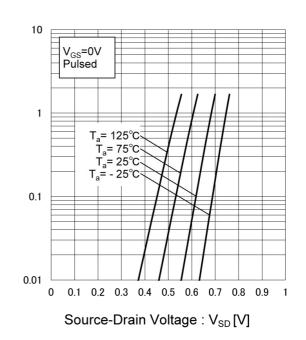


Fig.20 Source Current vs. Source Drain Voltage



Source Current : Is [A]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

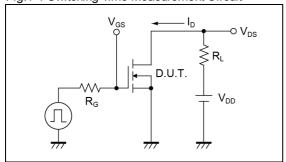


Fig.2-1 Gate Charge Measurement Circuit

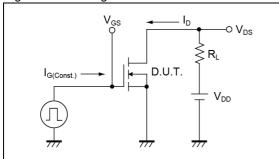


Fig.3-1 Avalanche Measurement Circuit

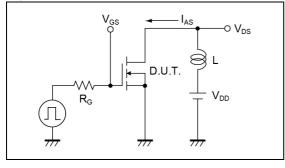


Fig.1-2 Switching Waveforms

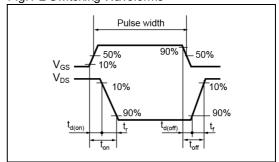


Fig.2-2 Gate Charge Waveform

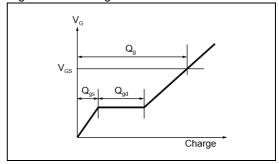
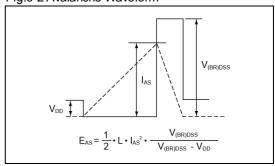


Fig.3-2 Avalanche Waveform



Notice

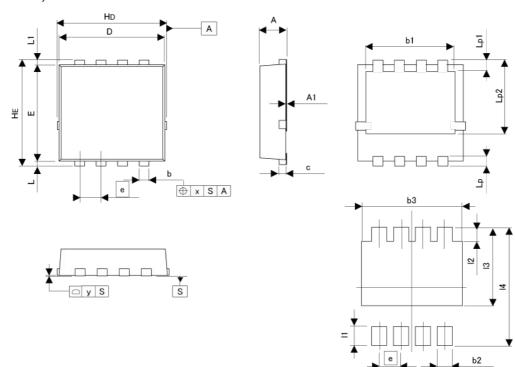
This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.



Dimensions

HSMT8

(3.3x3.3)



DIM	MILIME	TERS	INCI	HES
DIM	MIN	MAX	MIN	MAX
Α	0.70	0.90	0.028	0.035
A1	0.00	0.05	0.000	0.002
b	0.27	0.37	0.011	0.015
b1	2.50	2.70	0.098	0.106
С	0.10	0.30	0.004	0.012
D	3.10	3.30	0.122	0.130
E	2.90	3.10	0.114	0.122
е	0.	65	0.0	26
HD	3.20	3.40	0.126	0.134
HE	3.20	3.40	0.126	0.134
L	0.07	0.25	0.003	0.010
L1	0.07	0.25	0.003	0.010
Lp	0.20	0.40	0.008	0.016
Lp1	0.25	0.45	0.010	0.018
Lp2	2.20	2.40	0.087	0.094
Х	-	0.10	-	0.004
У	(I=)	0.10	-	0.004

DIM	MILIME	ETERS	INCHES		
DIIVI	MIN	MAX	MIN	MAX	
b2		0.47		0.019	
b3	0.70	2.70	-	0.106	
I1	-	0.50	-	0.020	
12	-	0.55	-	0.022	
13	(c.=.)	2.40	-	0.094	
14	121	3.40	-	0.134	

Dimension in mm/inches



Pattern of terminal position areas [Not a pattern of soldering pads]

Notice

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JAPAN	USA	EU	CHINA
CLASSⅢ	CL ACCIII	CLASS II b	CI VCCIII
CLASSIV	CLASSII	CLASSⅢ	CLASSⅢ

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 - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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